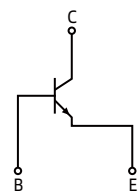


Features

- Collector current $I_C=1.5A$.
- Power amplifier applications.
- Complementary to SS8550.



SOT23



Equivalent Circuit

Absolute Maximum Ratings($T_A=25^{\circ}C$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	1.5	A
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	400	$^{\circ}C/W$
T_J, T_{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	$^{\circ}C/W$

Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise specified)

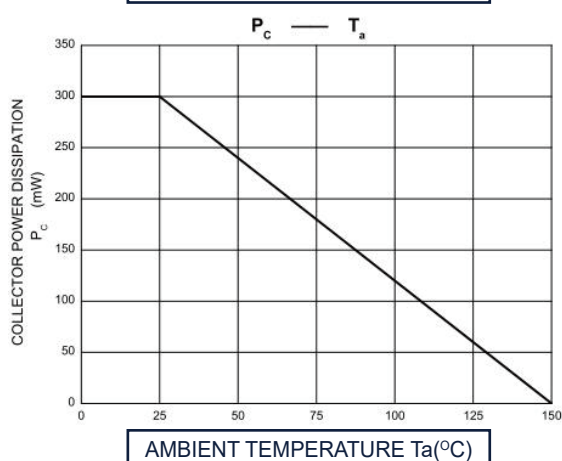
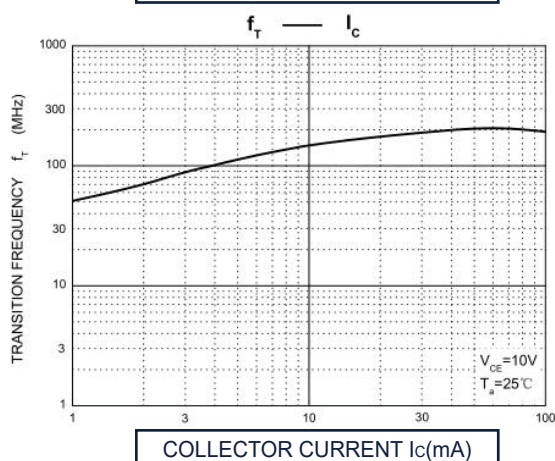
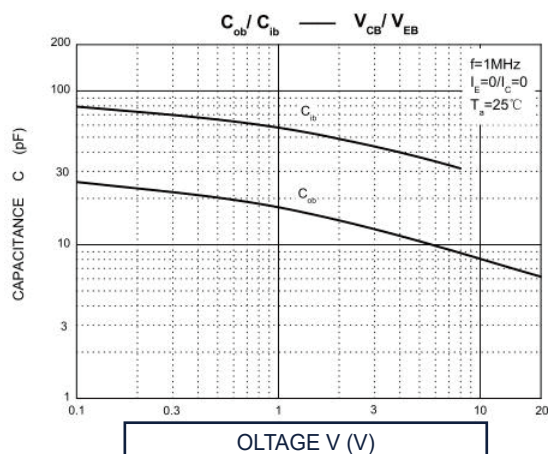
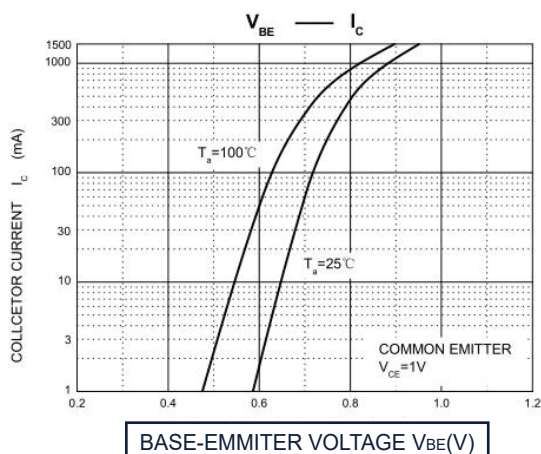
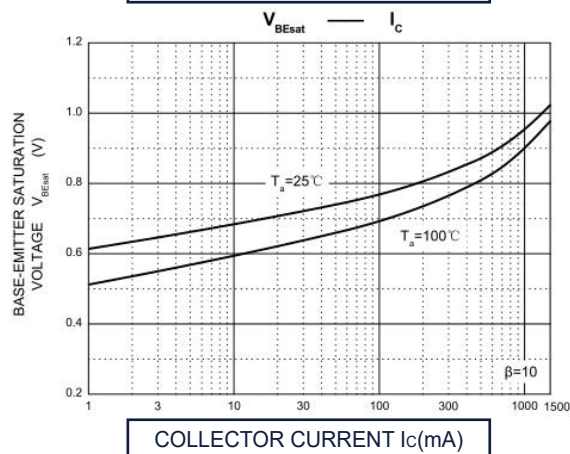
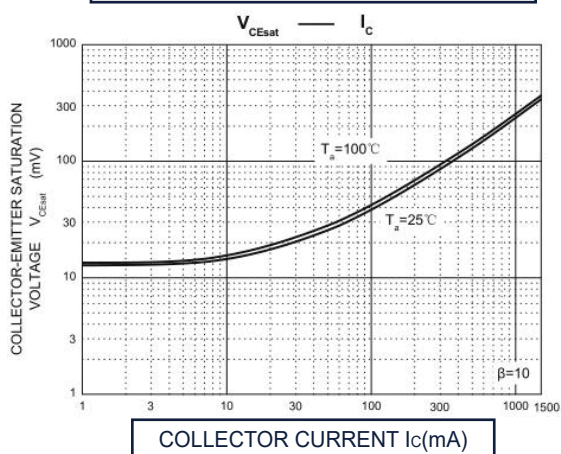
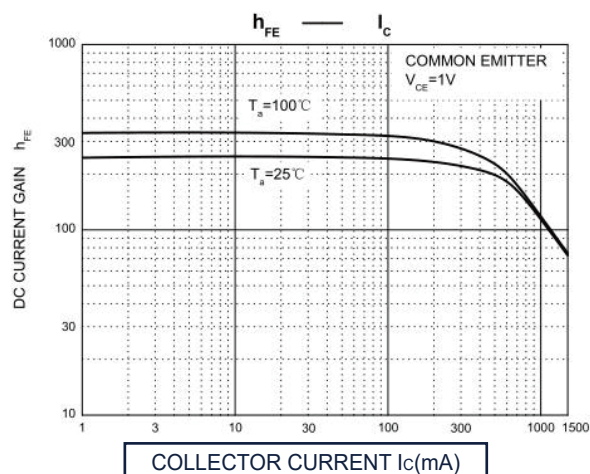
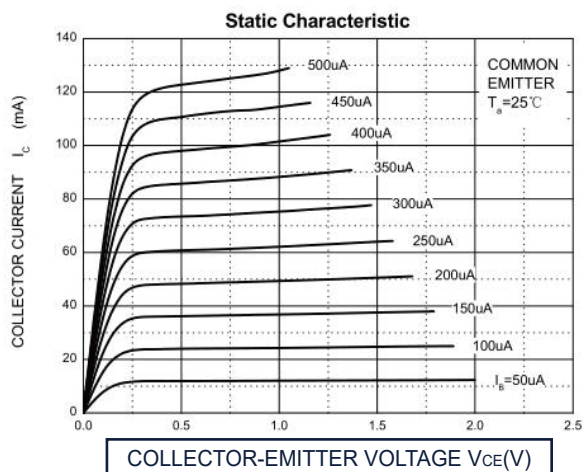
Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=100\mu A, I_E=0$	40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=0.1mA, I_B=0$	25			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A, I_C=0$	5			V
I_{CEO}	Collector cut-off current	$V_{CE}=20V, I_E=0$			100	nA
I_{CBO}	Collector cut-off current	$V_{CB}=40V, I_E=0$			100	nA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V, I_C=0$			100	nA
$h_{FE(1)}$	DC current gain(1)	$V_{CE}=1V, I_C=100mA$	200		350	
$h_{FE(2)}$	DC current gain(2)	$V_{CE}=1V, I_C=800mA$	40			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=800mA, I_B=80mA$			0.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage				1.2	V
f_T	Transition frequency	$V_{CE}=10V, I_C=50mA, f=30MHz$	100			MHz

Ordering information

Product ID	Pack	Naming rule	Marking	$h_{FE(1)}$	Qty(PCS)
SS8050	SOT23	SS8050 ↓ 产品名称 product name	Y1	200 ~ 350	3000

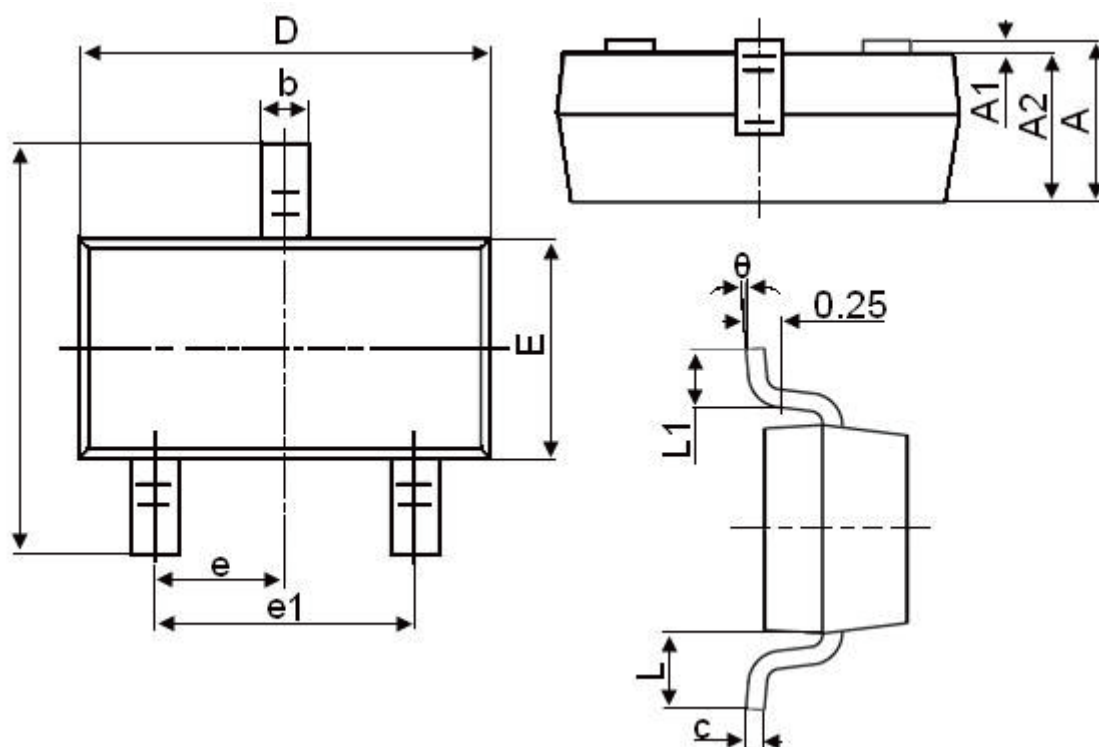


Typical Characteristics





SOT23 Package Outline Dimensions



Symbol	Dimensions in Millimeters	
	mm	
	Min	Max
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°